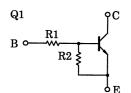
TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT Process) Silicon PNP Epitaxial Type (PCT Process)

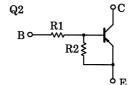
## **RN4985**

# Switching, Inverter Circuit, Interface Circuit And Driver Circuit Applications

- Includeing two devices in US6 (ultra super mini type with 6 leads)
- With built-in bias resistors
- Simplify circuit design
- Reduce a quantity of parts and manufacturing process

#### **Equivalent Circuit and Bias Resister Values**





R1:  $2.2k\Omega$ R2:  $47k\Omega$ (Q1, Q2 Common)

1

#### Q1 Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Collector-base voltage	$V_{CBO}$	50	V
Collector-emitter voltage	V <sub>CEO</sub>	50	V
Emitter-base voltage	V <sub>EBO</sub>	5	V
Collector current	IC	100	mA

#### Unit: mm 2.1 ± 0.1 1.25 ± 0.1 0~0.1 1. EMITTER 1 (E1) BASE 1 (B1) **COLLECTOR 2** (C2) **EMITTER 2** (E2) BASE 2 (B2) US6 **COLLECTOR 1** (C1) JEDEC EIAJ TOSHIBA 2-2J1A

Weight: 6.8mg

#### Q2 Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Collector-base voltage	$V_{CBO}$	-50	V
Collector-emitter voltage	$V_{CEO}$	-50	٧
Emitter-base voltage	V <sub>EBO</sub>	-5	٧
Collector current	IC	-100	mA

### Q1, Q2 Common Maximum Ratings (Ta = 25°C)

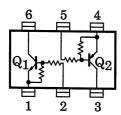
Characteristic	Symbol	Rating	Unit
Collector power dissipation	P <sub>C</sub> *	200	mW
Junction temperature	Tj	150	°C
Storage temperature range	T <sub>stg</sub>	-55~150	°C

<sup>\*</sup> Total rating

#### Marking



## **Equivalent Circuit (Top View)**



2

### Q1 Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I <sub>CBO</sub>	_	V <sub>CB</sub> = 50V, I <sub>E</sub> = 0	_	_	100	nA
Collector cut-on current	I <sub>CEO</sub>	_	V <sub>CE</sub> = 50V, I <sub>B</sub> = 0	_	-	500	
Emitter cut-off current	I <sub>EBO</sub>	_	$V_{EB} = 5V, I_C = 0$	0.078	_	0.145	mA
DC current gain	h <sub>FE</sub>	_	V <sub>CE</sub> = 5V, I <sub>C</sub> = 10mA	80	_	_	_
Collector-emitter saturation voltage	V <sub>CE (sat)</sub>	_	I <sub>C</sub> = 5mA, I <sub>B</sub> = 0.25mA	_	0.1	0.3	V
Input voltage (ON)	V <sub>I (ON)</sub>	_	V <sub>CE</sub> = 0.2V, I <sub>C</sub> = 5mA	0.6	_	1.1	V
Input voltage (OFF)	V <sub>I (OFF)</sub>	_	$V_{CE} = 5V, I_{C} = 0.1mA$	0.5	_	0.8	V
Transition frequency	f <sub>T</sub>	_	V <sub>CE</sub> = 10V, I <sub>C</sub> = 5mA	_	250	_	MHz
Collector output capacitance	C <sub>ob</sub>	_	V <sub>CB</sub> = 10V, I <sub>E</sub> = 0, f = 1 MHz	_	3	6	pF

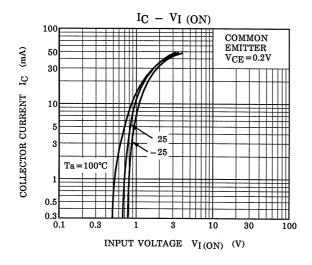
### Q2 Electrical Characteristics (Ta = 25°C)

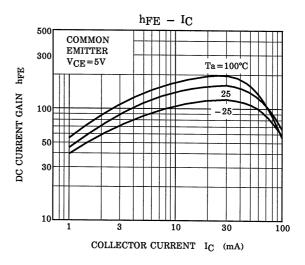
Characteristic	Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I <sub>CBO</sub>	_	$V_{CB} = -50V, I_E = 0$	_	_	-100	nA
Collector cut-on current	I <sub>CEO</sub>	_	$V_{CE} = -50V, I_B = 0$	_	_	-500	
Emitter cut-off current	I <sub>EBO</sub>	_	$V_{EB} = -5V, I_C = 0$	-0.078	_	-0.145	mA
DC current gain	h <sub>FE</sub>	_	$V_{CE} = -5V, I_{C} = -10mA$	80	_	_	-
Collector-emitter saturation voltage	V <sub>CE (sat)</sub>	_	$I_C = -5mA$ , $I_B = -0.25mA$	_	-0.1	-0.3	٧
Input voltage (ON)	V <sub>I (ON)</sub>	_	V <sub>CE</sub> = -0.2V, I <sub>C</sub> = -5mA	-0.6	_	-1.1	V
Input voltage (OFF)	V <sub>I (OFF)</sub>	_	$V_{CE} = -5V, I_{C} = -0.1mA$	-0.5	_	-0.8	V
Transition frequency	f <sub>T</sub>	_	$V_{CE} = -10V, I_{C} = -5mA$	_	200	_	MHz
Collector output capacitance	C <sub>ob</sub>	_	V <sub>CB</sub> = −10V, I <sub>E</sub> = 0	_	3	6	pF

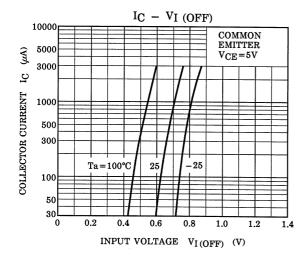
#### Q1, Q2 Common Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Circui t	Test Condition	Min	Тур.	Max	Unit
Input resistor	R1	_	_	1.54	2.2	2.86	kΩ
Resistor ratio	R1/R2	_		0.0421	0.0468	0.0515	_

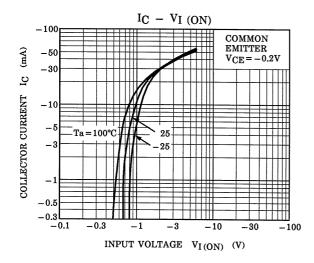
Q1

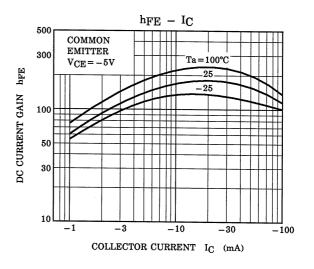


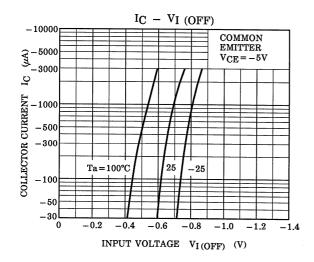




Q2







5

#### **RESTRICTIONS ON PRODUCT USE**

000707EAA

- TOSHIBA is continually working to improve the quality and reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to comply with the standards of safety in making a safe design for the entire system, and to avoid situations in which a malfunction or failure of such TOSHIBA products could cause loss of human life, bodily injury or damage to property. In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent TOSHIBA products specifications. Also, please keep in mind the precautions and conditions set forth in the "Handling Guide for Semiconductor Devices," or "TOSHIBA Semiconductor Reliability Handbook" etc..
- The TOSHIBA products listed in this document are intended for usage in general electronics applications (computer, personal equipment, office equipment, measuring equipment, industrial robotics, domestic appliances, etc.). These TOSHIBA products are neither intended nor warranted for usage in equipment that requires extraordinarily high quality and/or reliability or a malfunction or failure of which may cause loss of human life or bodily injury ("Unintended Usage"). Unintended Usage include atomic energy control instruments, airplane or spaceship instruments, transportation instruments, traffic signal instruments, combustion control instruments, medical instruments, all types of safety devices, etc.. Unintended Usage of TOSHIBA products listed in this document shall be made at the customer's own risk.
- The information contained herein is presented only as a guide for the applications of our products. No
  responsibility is assumed by TOSHIBA CORPORATION for any infringements of intellectual property or other
  rights of the third parties which may result from its use. No license is granted by implication or otherwise under
  any intellectual property or other rights of TOSHIBA CORPORATION or others.
- The information contained herein is subject to change without notice.